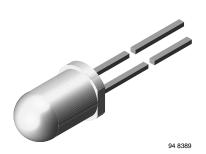
HALOGEN FREE



Vishay Semiconductors

High Speed Infrared Emitting Diode, 890 nm, GaAlAs Double Hetero



DESCRIPTION

TSHF6210 is an infrared, 890 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted plastic package.

FEATURES

Package type: leaded
Package form: T-1¾
Dimensions (in mm): Ø 5
Peak wavelength: λ_p = 890 nm

· High reliability

High radiant power

• High radiant intensity

• Angle of half intensity: $\varphi = \pm 10^{\circ}$

· Low forward voltage

• Suitable for high pulse current operation

High modulation bandwidth: f_c = 12 MHz

· Good spectral matching with Si photodetectors

 Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC

• Halogen-free according to IEC 61249-2-21 definition

APPLICATIONS

- Infrared high speed remote control and free air data transmission systems with high modulation frequencies or high data transmission rate requirements
- Transmission systems according to IrDA requirements and for carrier frequency based systems (e.g. ASK/FSK coded, 450 kHz or 1.3 MHz)
- · Smoke-automatic fire detectors

PRODUCT SUMMARY					
COMPONENT	I _e (mW/sr)	φ (deg)	λ _P (nm)	t _r (ns)	
TSHF6210	180	± 10	890	30	

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION				
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM	
TSHF6210	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾	

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		V _R	5	V	
Forward current		l _F	100	mA	
Peak forward current	$t_p/T = 0.5, t_p = 100 \mu s$	I _{FM}	200	mA	
Surge forward current	t _p = 100 μs	I _{FSM}	1.5	Α	
Power dissipation		P _V	160	mW	
Junction temperature		Tj	100	°C	
Operating temperature range		T _{amb}	- 40 to + 85	°C	
Storage temperature range		T _{stg}	- 40 to + 100	°C	
Soldering temperature	$t \le 5$ s, 2 mm from case	T _{sd}	260	°C	
Thermal resistance junction/ambient	J-STD-051, leads 7 mm soldered on PCB	R _{thJA}	230	K/W	

Note

T_{amb} = 25 °C, unless otherwise specified

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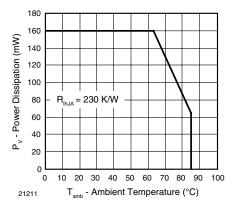


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

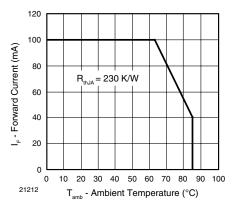


Fig. 2 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Family altered	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	V _F		1.4	1.6	V
Forward voltage	$I_F = 1 \text{ A}, t_p = 100 \ \mu \text{s}$	V _F		2.3		V
Temperature coefficient of V _F	I _F = 1 mA	TK _{VF}		- 1.8		mV/K
Reverse current	V _R = 5 V	I _R			10	μΑ
Junction capacitance	V _R = 0 V, f = 1 MHz, E = 0	C _j		125		pF
Dadient intensity	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	l _e	120	180	360	mW/sr
Radiant intensity	I _F = 1 A, t _p = 100 μs	l _e		1800		mW/sr
Radiant power	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	φ _e		50		mW
Temperature coefficient of φ _e	I _F = 100 mA	TKφe		- 0.35		%/K
Angle of half intensity		φ		± 10		deg
Peak wavelength	I _F = 100 mA	λρ		890		nm
Spectral bandwidth	I _F = 100 mA	Δλ		40		nm
Temperature coefficient of λ_p	I _F = 100 mA	TKλ _p		0.25		nm/K
Rise time	I _F = 100 mA	t _r		30		ns
Fall time	I _F = 100 mA	t _f		30		ns
Cut-off frequency	I _{DC} = 70 mA, I _{AC} = 30 mA pp	f _c		12		MHz
Virtual source diameter		d		3.7		mm

Note

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High Speed Infrared Emitting Diode, Vishay Semiconductors 890 nm, GaAlAs Double Hetero

BASIC CHARACTERISTICS

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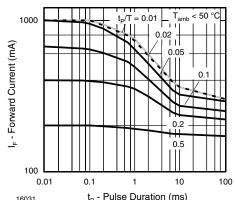


Fig. 3 - Pulse Forward Current vs. Pulse Duration

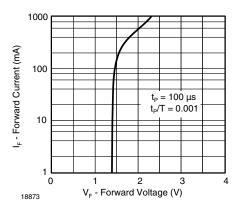


Fig. 4 - Forward Current vs. Forward Voltage

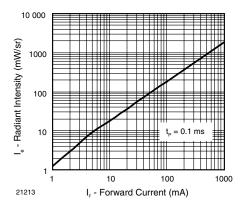


Fig. 5 - Radiant Intensity vs. Forward Current

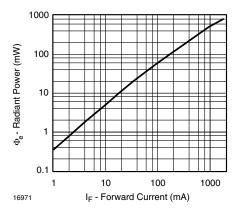


Fig. 6 - Radiant Power vs. Forward Current

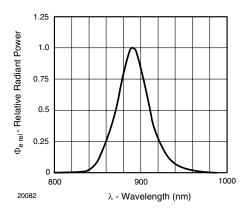


Fig. 7 - Relative Radiant Power vs. Wavelength

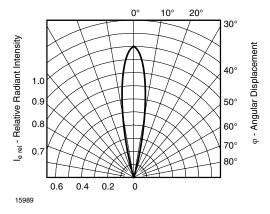
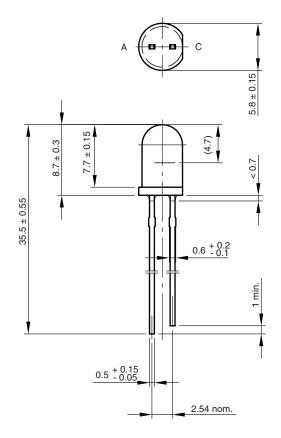


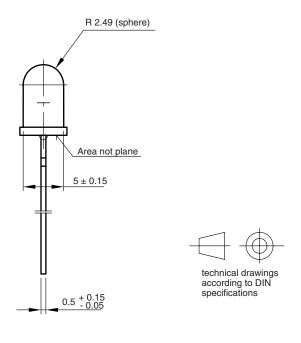
Fig. 8 - Relative Radiant Intensity vs. Angular Displacement

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PACKAGE DIMENSIONS in millimeters





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